



Product Discontinuation Notice

October 30, 2010

Photomicrosensors

No. A1PH-095252(E)

Discontinuation Notice of Photomicrosensors.

EE-SB5V series

Product Discontinuation

Recommended Replacement



EE-SB5V Series



Please contact the appropriate division EE-SY672 (except the EE-SB5M-E)

Discontinuation date: The end of May, 2010

Caution on recommended replacement

Our Amplified photomicrosensors, model EE-SB5V series will be discontinued at the end of May, 2010. We recommend Amplified photomicrosensors, type EE-SY672 for replacement of them (except the EE-SB5V-E). And we recommend to change your products design or to order it collectively including a necessary amount in the future by May, 2010.

Difference from discontinued product

Model	Body	Dimensions	Wire	Mounting	Characteristics	Operation	Operation
	Color		connection	Dimentions		ratings	methods
EE-SY672	**	*		*	*	*	**

^{**:} Fully compatible

^{* :} The change is a little / Almost compatible

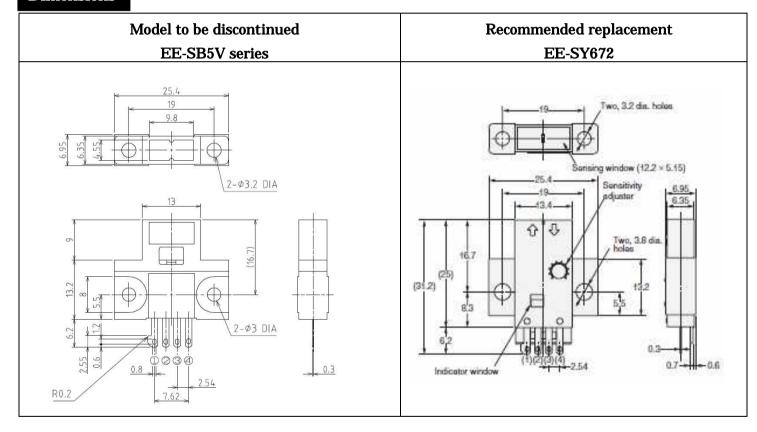
^{--:} Not compatible

^{- :} No corresponding specification

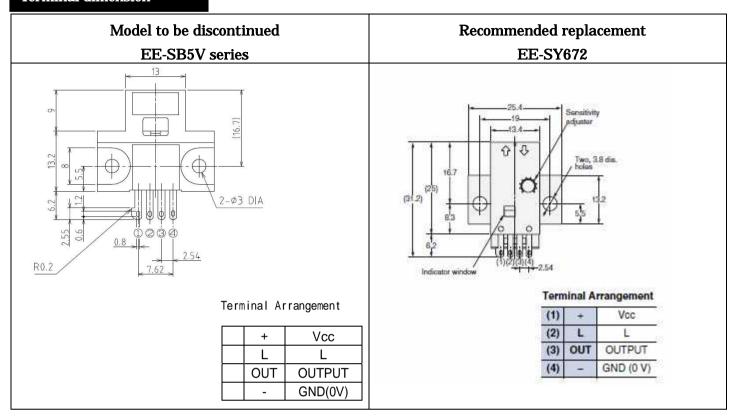
Product Discontinuation and recommended replacement

Pr	oduct discontinuation	Rec	Recommended replacement		
Model	Product code	Model	Product code		
EE-SB5V	EESB1010G	EE-SY672	EESY1124M		
EE-SB5V-F	EESB5052D	No recommended	No recommended replacement		
EE-SB5V-P1	EESB5054M	EE-SY672	EESY1124M		
EE-SB5VC	EESB2010B	EE-SY672	EESY1124M		

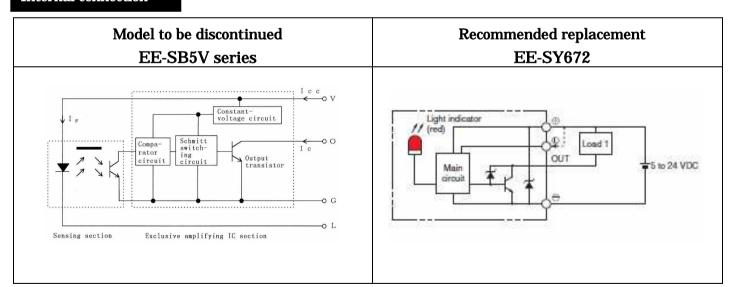
Dimensions



Terminal dimension



Internal connection



Characteristics

Item		Model to be discontinued		Recommended replacement	
		EE-SB5V	EE-SB5VC	EE-SY672	
Sensing distance		5mm (Reflection factor 90%)		1 to 5mm (Reflection factor 90%)	
Differentia	l distance	0.1mm		0.5mm	
Light source	ce	GaAs infrared LED		GaAs infrared LED	
Cumpler scale	ho ero	5-10% to 15+10% VDC		5-10% to 24+10% VDC	
Supply vol	tage	Ripple (p-p): 10% MAX.		Ripple (p-p): 10% MAX.	
Current co	nsumption	48mA MAX.		40mA MAX.	
		Load power supply voltage: 5 to 24VDC		Load power supply voltage: 5 to 24VDC	
		80mA load current wit	th a residual	100mA load current with a residual	
Control out	tput	voltage 0.8V MAX.		voltage 0.8V MAX.	
		40mA load current with a residual		40mA load current with a residual	
		voltage 0.4V MAX.		voltage 0.4V MAX.	
	Stage of output	OFF	ON	OFF	ON
G. 6	transistor when			(Terminal [L]	(Terminal [L]
Stage of	object is not sensed			is short-circuited)	is opened)
output transistor	Stage of output	ON	OFF	ON	OFF
ti ansistoi	transistor when			(Terminal [L]	(Terminal [L]
	object is sensed			is short-circuited)	is opened)
Response f	requency	50Hz		50Hz	
Ambient	temperature	Operating : -25 ~ +55		Operating : -25 ~ +55	
range	•	Storage : -30 ~ +80		Storage : -30 ~ +80	
A		Operating: 45 ~ 85%RH		Operating: 5~85%RH	
Ambient no	umidity range	Storage : 35 ~ 95%RH		Storage : 5 ~ 95%RH	
		Destruction:		Destruction:	
Vibration resistance		20 to 2000 Hz		20 to 2000 Hz	
		(Peak acceleration: 200m/s²)		(Peak acceleration: 100m/s²)	
		1.5mm double amplitude for 4cycle		1.5mm double amplitude for 2h	
		(4min periods) each in X, Y and Z		(4min periods) each in X, Y and Z	
		directions		directions	
Shock resistance		Destruction:		Destruction:	
		15000m/S ² for 3 times each in X, Y		500m/S ² for 3 times each in X, Y and	
		and Z directions		Z directions	

Item		Model to be discontinued EE-SB5V-P1	Recommended replacement EE-SY672	
Sensing distance		5mm (Reflection factor 90%)	1 to 5mm (Reflection factor 90%)	
Differential distance		0.1mm	0.5mm	
Light source		GaAs infrared LED	GaAs infrared LED	
Supply voltage		24 ± 10% VDC	5-10% to 24+10% VDC	
			Ripple (p-p): 10% MAX.	
Current con	nsumption	-	40mA MAX.	
		Load power supply voltage: 5 to 24VDC	Load power supply voltage: 5 to 24VDC	
		10mA load current with a residual	100mA load current with a residual	
Control out	put	voltage 0.3V MAX.	voltage 0.8V MAX.	
			40mA load current with a residual	
	Stage of output	OFF	voltage 0.4V MAX.	ON
	transistor when	OFF	(Terminal [L]	(Terminal [L]
Stage of	object is not		is short-circuited)	is opened)
output	sensed		is short-circuited)	is opened)
transistor	Stage of output	ON	ON	OFF
	transistor when		(Terminal [L]	(Terminal [L]
	object is sensed		is short-circuited)	is opened)
Response fi	requency	50Hz	50Hz	
Ambient	temperature	Operating : -25 ~ +55	Operating : -25 ~ +55	
range		Storage : -30 ~ +80	Storage : -30 ~ +80	
A b 4 b -	!	Operating: 45 ~ 85%RH	Operating: 5 ~ 85%RH	
Ambient nu	umidity range	Storage : 35 ~ 95%RH	Storage: 5 ~ 95%RH	
		Destruction:	Destruction:	
		20 to 2000 Hz	20 to 2000 Hz	
Vibration resistance		(Peak acceleration: 200m/s²)	(Peak acceleration: 100m/s²)	
		1.5mm double amplitude for 4cycle	1.5mm double amplitude for 2h	
		(4min periods) each in X, Y and Z	(4 \min periods) each in X, Y and Z	
		directions	directions	
		Destruction:	Destruction:	
Shock resistance		15000m/S ² for 3 times each in X, Y	500m/S ² for 3 times each in X, Y and	
		and Z directions	Z directions	

Item		Model to be discontinued EE-SB5V-E	Recommended replacement No type
Sensing distance		19mm (Reflection factor 90%)	
Differential distance		0.1mm	
Light source		GaAs infrared LED]
Supply voltage		5-10% to 15+10% VDC	
Suppry voita	ige	Ripple (p-p): 10% MAX.	
Current cons	sumption	48mA MAX.	
Control output		Load power supply voltage: 5 to 24VDC 80mA load current with a residual voltage 0.8V MAX.	
		40mA load current with a residual voltage 0.4V MAX.	
Stage of output	Stage of output transistor when object is not sensed	OFF	
transistor	Stage of output transistor when object is sensed	ON	
Response fre	equency	50Hz	
Ambient temperature range		Operating : -25 ~ +55 Storage : -30 ~ +80	
Ambient humidity range		Operating: 45 ~ 85%RH Storage: 85 ~ 95%RH	
Vibration resistance		Destruction: 20 to 2000 Hz	
		(Peak acceleration: 200m/s²) 1.5mm double amplitude for 4cycle	
		(4min periods) each in X, Y and Z directions	
Shock resistance		Destruction: 15000m/S² for 3 times each in X, Y and Z directions	